

Wen Pengyan

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/9247061/publications.pdf>

Version: 2024-02-01

11
papers

79
citations

1478505

6
h-index

1474206

9
g-index

11
all docs

11
docs citations

11
times ranked

128
citing authors

#	ARTICLE	IF	CITATIONS
1	Degradation study of InGaN-based laser diodes grown on Si. Journal Physics D: Applied Physics, 2020, 53, 395103.	2.8	5
2	Total-InGaN-thickness dependent Shockley-Read-Hall recombination lifetime in InGaN quantum wells. Journal of Applied Physics, 2020, 127, .	2.5	8
3	Rapid degradation of InGaN/GaN green laser diodes. Superlattices and Microstructures, 2020, 142, 106517.	3.1	4
4	Strain-Related Degradation of GaN-Based Blue Laser Diodes. IEEE Journal of Selected Topics in Quantum Electronics, 2019, 25, 1-5.	2.9	0
5	Significant increase of quantum efficiency of green InGaN quantum well by realizing step-flow growth. Applied Physics Letters, 2017, 111, 112102.	3.3	15
6	Asymmetrical quantum well degradation of InGaN/GaN blue laser diodes characterized by photoluminescence. Applied Physics Letters, 2017, 111, 212102.	3.3	7
7	Green laser diodes with low operation voltage obtained by suppressing carbon impurity in AlGaIn: Mg cladding layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 245-247.	0.8	9
8	Investigation of InGaN/GaN laser degradation based on luminescence properties. Journal of Applied Physics, 2016, 119, .	2.5	14
9	Catastrophic Degradation of InGaN/GaN Blue Laser Diodes. IEEE Transactions on Device and Materials Reliability, 2016, 16, 638-641.	2.0	3
10	Investigation of rapid degradation in GaN-based blue laser diodes. Superlattices and Microstructures, 2016, 99, 72-76.	3.1	8
11	Enhanced temperature characteristic of InGaN/GaN laser diodes with uniform multiple quantum wells. Semiconductor Science and Technology, 2015, 30, 125015.	2.0	6